In The Claims

Please cancel claims 2-4, 10, 12-13 and 19-20 without prejudice to or disclaimer of the subject matter contained therein.

Please amend the claims as follows:

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1. (Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type formed additionally between the first active regions, wherein the second active region includes an n+ junction connected to Vcc reference voltage or a p+ junction connected to ground Vss; and

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions.

A4

5. (Amended) The device of claim 1, further comprising:

a plurality of drain regions formed in each of the first active regions.

A5

8. (Amended) The device of claim 1, wherein the first and second active regions and the gates extend substantially parallel to each other.

11. (Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions; and

at least one predetermined conductive type second active region formed between two of the first active regions, wherein the predetermined conductive type second active region is an n+ junction connected to Vcc reference voltage.

17. (Amended) The device of claim 11, further comprising:

a third active region surrounding completely the first and second active regions.

18. (Amended) A multi-finger type ESD protection device comprising:

a semiconductor substrate;

a plurality of first active regions formed separately on the semiconductor substrate;

a plurality of gates formed in each of the first active regions;

at least one second active region of a predetermined conductive type, formed between the first active regions, wherein the predetermined conductive type second active region includes a p+ junction connected to ground Vss; and

A7

a third active region surrounding the first and second active regions and being of conductivity type different from that of the first active regions.

Please add the following claims.

--21. (NEW) The device of claim 1, wherein the third active region surrounds completely the first and second active regions.

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22. (NEW) The device of claim 21, wherein the first active region has a ring configuration.

23. (NEW) The device of claim 1, wherein the first active region is of p conductive type.

24. (NEW) The device of claim 18, further comprising:

drain regions formed at n+ junctions of both end portions of the first active regions.

25. (NEW) The device of claim 18, further comprising:

source regions each formed between the gates in each of the first active regions.

26. (NEW) The device of claim 18, wherein the first and second active regions and the gates extend substantially parallel to each other and have a substantially same shape.

A8

27. (NEW) The device of claim 18, wherein spaces are provided between the first and second active regions.--